

STD25NF10L

N-channel 100V - 0.030Ω - 25A - DPAK Low gate charge STripFET™ II Power MOSFET

General features

Туре	V _{DSS}	R _{DS(on)}	I _D
STD25NF10L	100V	< 0.035Ω	25A

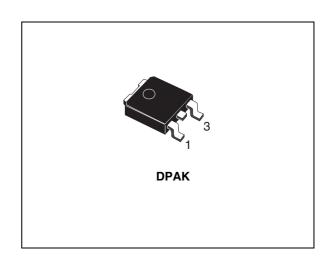
- Exceptional dv/dt capability
- 100% avalanche tested
- Low threshold device
- Logic level device

Description

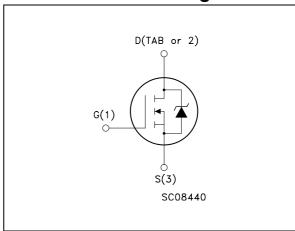
This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

Applications

■ Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging	
STD25NF10LT4	D25NF10L	DPAK	Tape & reel	

Contents STD25NF10L

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STD25NF10L Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V _{DS}	Drain-source voltage (V _{GS} = 0)	100	V	
V _{DGR}	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	100	V	
V _{GS}	Gate- source voltage	± 16	V	
I _D ⁽¹⁾	Drain current (continuous) at T _C = 25°C	25	Α	
I _D	Drain current (continuous) at T _C = 100°C	21	А	
I _{DM} ⁽²⁾	Drain current (pulsed)	100	Α	
P _{tot}	Total dissipation at T _C = 25°C	100	W	
	Derating Factor	0.67	W/°C	
dv/dt ⁽³⁾	Peak diode recovery avalanche energy	20	V/ns	
E _{AS} (4)	Single pulse avalanche energy	450		
T _{stg}	Storage temperature			
Tj	Max. operating junction temperature	-55 to 175	°C	

- 1. Current limited by package
- 2. Pulse width limited by safe operating area.
- 3. I_{SD} \leq 25A, di/dt \leq 300A/ μ s, V_{DD} = $V(_{BR)DSS}$, $T_j \leq T_{JMAX}$
- 4. Starting $T_i = 25$ °C, $I_D = 12.5 \text{A V}_{DD} = 50 \text{V}$

Table 2. Thermal data

Rthj-case	Thermal resistance junction-case max	1.5	°C/W
Rthj-pcb	Thermal resistance junction-pcb max (1)	100	°C/W
T _J	Maximum lead temperature for soldering purpose	275	°C

1. When Mounted on 1 inch2 FR-4 board, 2 oz of Cu.

Electrical characteristics STD25NF10L

2 Electrical characteristics

(T_{CASE} =25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating, T_{C} = 125°C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		2.5	V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 10V, I_D = 12.5A$ $V_{GS} = 4.5V, I_D = 12.5A$		0.030 0.035	0.035 0.040	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} (1)	Forward transconductance	V _{DS} = 15V, I _D = 12.5A		24		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		1710 250 110		pF pF pF
$\begin{array}{c} t_{\text{d(on)}} \\ t_{\text{r}} \\ t_{\text{d(off)}} \\ t_{\text{f}} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 50V, I_D = 12.5A R_G = 4.7 Ω V_{GS} = 5V (see <i>Figure 13</i>)		20 40 58 20		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 80V, I_{D} = 25A,$ $V_{GS} = 5V, R_{G} = 4.7\Omega$ (see <i>Figure 14</i>)		38 8.5 21	52	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				25 100	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 25A, V _{GS} = 0			1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 25A$, di/dt = 100A/ μ s, $V_{DD} = 50V$, $T_{j} = 150$ °C (see <i>Figure 15</i>)		88 317 7.2		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5 %

Electrical characteristics STD25NF10L

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

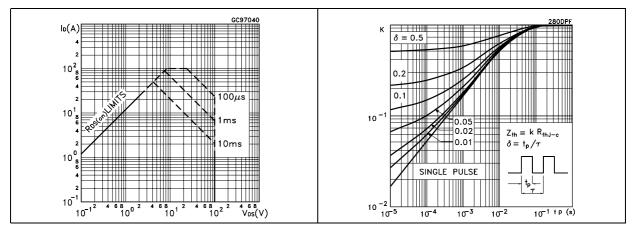


Figure 3. Output characterisics

Figure 4. Transfer characteristics

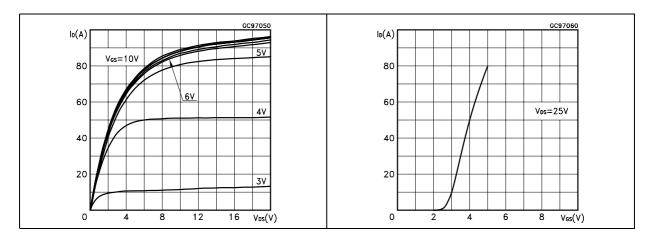
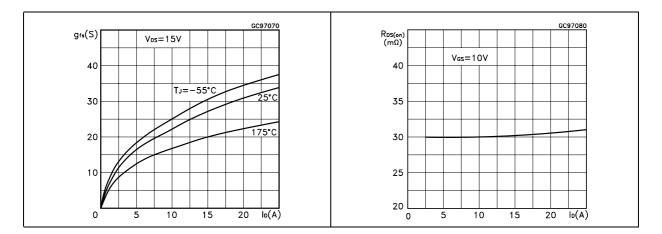


Figure 5. Transconductance

Figure 6. Static drain-source on resistance



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Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

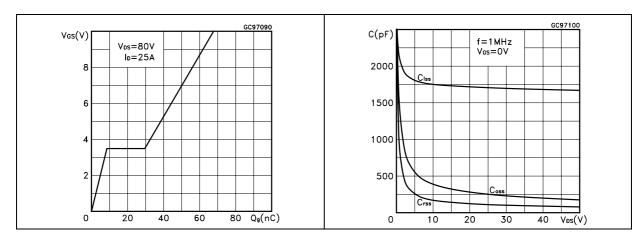


Figure 9. Normalized gate threshold voltage vs temperature

Figure 10. Normalized on resistance vs temperature

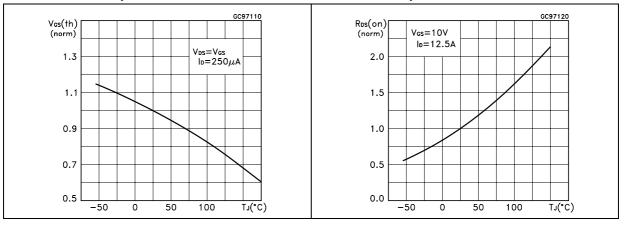
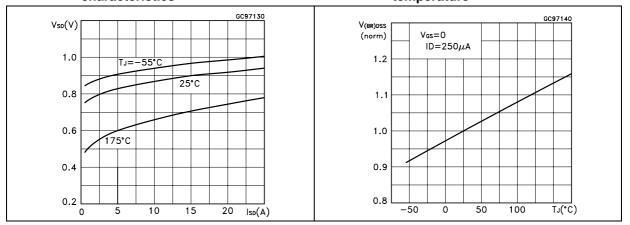


Figure 11. Source-drain diode forward characteristics

Figure 12. Normalized breakdown voltage vs temperature



Test circuit STD25NF10L

3 Test circuit

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

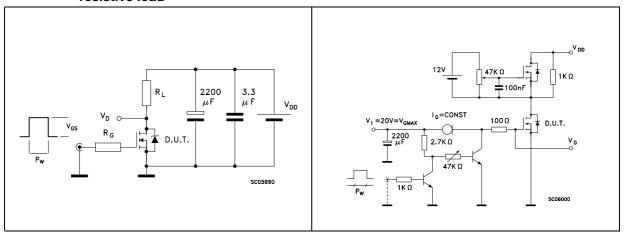


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped Inductive load test circuit

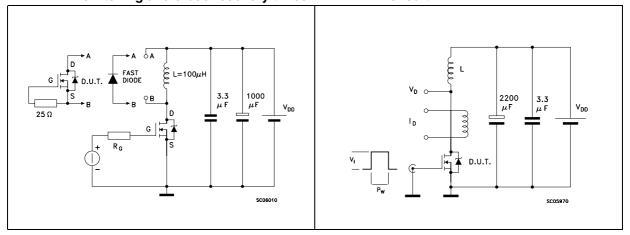
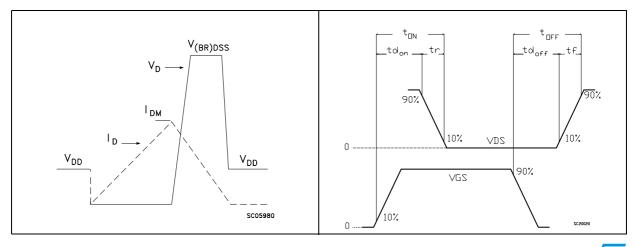


Figure 17. Unclamped inductive waveform

Figure 18. Switching time waveform



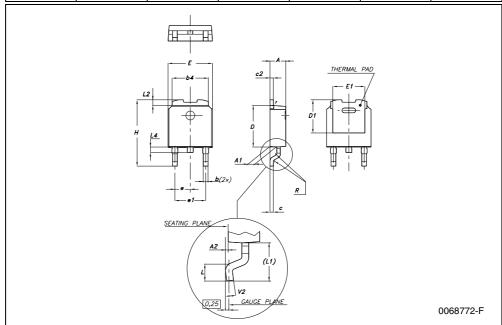
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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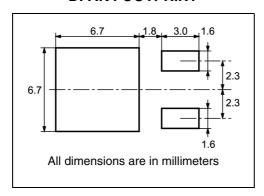
DPAK MECHANICAL DATA

DIM		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
Е	6.4		6.6	0.252	0	
E1		4.7			0.185	
е		2.28			0.090	
e1	4.4		4.6	0.173	0.	
Н	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

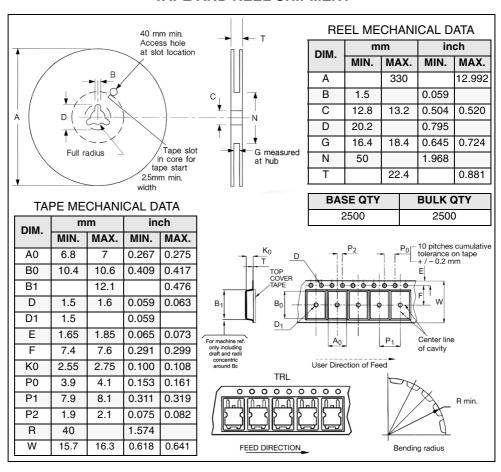


5 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



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Revision history STD25NF10L

6 Revision history

Table 6. Revision history

Date	Revision	Changes
21-Jun-2004	1	Preliminary version
03-Jun-2006	2	New template, no content change

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